

Refine Search

Search Results -

Terms	Documents
L39	0

Database: US Pre-Grant Publication Full-Text Database
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 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search: L40

Search History

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<u>Set</u>	<u>Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set</u>
				result set
side by side				
DB=TDBD; PLUR=YES; OP=OR				
<u>L40</u>	<u>L39</u>		0	<u>L40</u>
DB=DWPI; PLUR=YES; OP=OR				
<u>L39</u>	<u>L38</u>		0	<u>L39</u>
DB=JPAB; PLUR=YES; OP=OR				
<u>L38</u>	<u>L37</u>		0	<u>L38</u>
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<u>L37</u>	<u>L36</u>		0	<u>L37</u>
DB=USOC; PLUR=YES; OP=OR				
<u>L36</u>	<u>L35</u>		0	<u>L36</u>
DB=PGPB; PLUR=YES; OP=OR				
<u>L35</u>	<u>L34</u>		0	<u>L35</u>
DB=USPT; PLUR=YES; OP=OR				
<u>L34</u>	L32 same (graded or "nitrogen oncentration")		0	<u>L34</u>

<u>L33</u>	L32 same graded or (nitrogen near7 (concentration))	12332	<u>L33</u>
<u>L32</u>	"gate dielectric" near7 (metal near3 nitride)	27	<u>L32</u>
	<i>DB=TDBD; PLUR=YES; OP=OR</i>		
<u>L31</u>	L30	0	<u>L31</u>
	<i>DB=DWPI; PLUR=YES; OP=OR</i>		
<u>L30</u>	L29	0	<u>L30</u>
	<i>DB=JPAB; PLUR=YES; OP=OR</i>		
<u>L29</u>	L28	0	<u>L29</u>
	<i>DB=EPAB; PLUR=YES; OP=OR</i>		
<u>L28</u>	L27	0	<u>L28</u>
	<i>DB=USOC; PLUR=YES; OP=OR</i>		
<u>L27</u>	L26	0	<u>L27</u>
	<i>DB=PGPB; PLUR=YES; OP=OR</i>		
<u>L26</u>	L25	0	<u>L26</u>
	<i>DB=USPT; PLUR=YES; OP=OR</i>		
<u>L25</u>	L22 and ("gate dielectric" near4 graded near5 nitrogen)	0	<u>L25</u>
<u>L24</u>	L22 and ("gate dielectric" near3 "nitrogen concentration")	0	<u>L24</u>
<u>L23</u>	L22 and "nitrogen concentration"	202	<u>L23</u>
<u>L22</u>	("gate dielectric" or "gate insulation") near5 ((nitrogen and metal) or (metal near2 oxy near2 nitride))	1966	<u>L22</u>
<u>L21</u>	("gate dielectric" or "gate insulation") near7 ((nitrogen and metal) or (metal near2 oxy near2 nitride))	2688	<u>L21</u>
<u>L20</u>	("gate dielectric" or "gate insulation") same ((nitrogen and metal) or (metal near2 oxy near2 nitride))	7755	<u>L20</u>
<u>L19</u>	6020243	45	<u>L19</u>
	<i>DB=PGPB; PLUR=YES; OP=OR</i>		
<u>L18</u>	L17	0	<u>L18</u>
	<i>DB=TDBD; PLUR=YES; OP=OR</i>		
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	<i>DB=DWPI; PLUR=YES; OP=OR</i>		
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	<i>DB=JPAB; PLUR=YES; OP=OR</i>		
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	<i>DB=EPAB; PLUR=YES; OP=OR</i>		
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<u>L13</u>	L12	0	<u>L13</u>
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<u>L12</u>	L11	0	<u>L12</u>
	<i>DB=USOC; PLUR=YES; OP=OR</i>		
<u>L11</u>	L8 and capacitor	0	<u>L11</u>
<u>L10</u>	L9	0	<u>L10</u>
	<i>DB=USPT; PLUR=YES; OP=OR</i>		

<u>L9</u>	L8 and "first barrier metal"	0	<u>L9</u>
<u>L8</u>	L7 and fill	2	<u>L8</u>
<u>L7</u>	L6 and ((via\$ or feedthrough) near5 interlayer)	5	<u>L7</u>
<u>L6</u>	L5 and (interlayer near5 "etch stop")	9	<u>L6</u>
<u>L5</u>	L3 and ("etch stop" near5 (metal or conductor))	227	<u>L5</u>
<u>L4</u>	L3 and ("etch stop": near5 (metal or conductor))	227	<u>L4</u>
<u>L3</u>	L1 and ((metal or conductor) near4 insulat\$5)	23211	<u>L3</u>
<u>L2</u>	L1 and (metal near4 insulat\$5)	16944	<u>L2</u>
<u>L1</u>	(insulat\$5 near10 substrate)	82819	<u>L1</u>

END OF SEARCH HISTORY

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Search Results -

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L30	0

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Search:

Refine Search**Recall Text****Clear****Interrupt**

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Set
Name **Query**

side by
side

DB=TDBD; PLUR=YES; OP=OR

L31 L30

0 L31

DB=DWPI; PLUR=YES; OP=OR

L30 L29

0 L30

DB=JPAB; PLUR=YES; OP=OR

L29 L28

0 L29

DB=EPAB; PLUR=YES; OP=OR

L28 L27

0 L28

DB=USOC; PLUR=YES; OP=OR

L27 L26

0 L27

DB=PGPB; PLUR=YES; OP=OR

L26 L25

0 L26

DB=USPT; PLUR=YES; OP=OR

L25 L22 and ("gate dielectric" near4 graded near5 nitrogen)

0 L25

<u>L24</u>	L22 and ("gate dielectric" near3 "nitrogen concentration")	0	<u>L24</u>
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<u>L19</u>	6020243	45	<u>L19</u>
<i>DB=PGPB; PLUR=YES; OP=OR</i>			
<u>L18</u>	L17	0	<u>L18</u>
<i>DB=TDBD; PLUR=YES; OP=OR</i>			
<u>L17</u>	L16	0	<u>L17</u>
<i>DB=DWPI; PLUR=YES; OP=OR</i>			
<u>L16</u>	L15	0	<u>L16</u>
<i>DB=JPAB; PLUR=YES; OP=OR</i>			
<u>L15</u>	L14	0	<u>L15</u>
<i>DB=EPAB; PLUR=YES; OP=OR</i>			
<u>L14</u>	L13	0	<u>L14</u>
<u>L13</u>	L12	0	<u>L13</u>
<i>DB=USPT; PLUR=YES; OP=OR</i>			
<u>L12</u>	L11	0	<u>L12</u>
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<u>L11</u>	L8 and capacitor	0	<u>L11</u>
<u>L10</u>	L9	0	<u>L10</u>
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<u>L4</u>	L3 and ("etch stop": near5 (metal or conductor))	227	<u>L4</u>
<u>L3</u>	L1 and ((metal or conductor) near4 insulat\$5)	23211	<u>L3</u>
<u>L2</u>	L1 and (metal near4 insulat\$5)	16944	<u>L2</u>
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